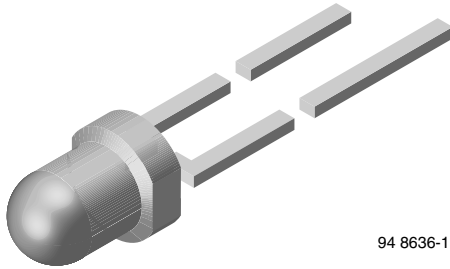


## Infrared Emitting Diode, 950 nm, GaAs



94 8636-1

### DESCRIPTION

TSUS4300 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue tinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing$  3
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 16^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- Emitter in reflective sensors

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSUS4300	18	$\pm 16$	950	800

#### Note

- Test conditions see table “Basic Characteristics”

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS4300	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1
TSUS4300-ASZ	Ammopack	MOQ: 10 000 pcs, 2000 pcs/box	T-1

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	2	A
Power dissipation		$P_V$	170	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	-40 to +85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-40 to +100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	300	K/W

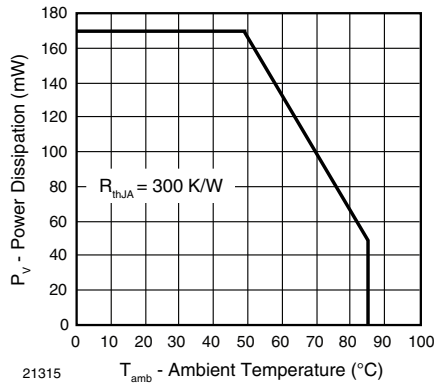


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

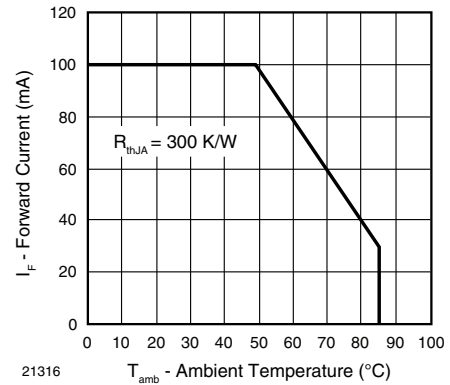


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$V_F$	-	1.3	1.7	V
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$	-	2.2	-	V
Temperature coefficient of $V_F$	$I_F = 100\text{ mA}$	$TK_{V_F}$	-	-1.3	-	mV/K
Reverse current	$V_R = 5\text{ V}$	$I_R$	-	-	100	$\mu\text{A}$
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	$V_{(BR)}$	5	40	-	
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_j$	-	30	-	pF
Radiant intensity	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$	7	18	35	mW/sr
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$	-	160	-	mW/sr
Radiant power	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\phi_e$	-	20	-	mW
Temperature coefficient of $\phi_e$	$I_F = 20\text{ mA}$	$TK_{\phi_e}$	-	-0.8	-	%/K
Angle of half intensity		$\varphi$	-	$\pm 16$	-	deg
Peak wavelength	$I_F = 100\text{ mA}$	$\lambda_p$	-	950	-	nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$	-	50	-	nm
Temperature coefficient of $\lambda_p$	$I_F = 100\text{ mA}$	$TK_{\lambda_p}$	-	0.2	-	nm/K
Rise time	$I_F = 100\text{ mA}$	$t_r$	-	800	-	ns
	$I_F = 1.5\text{ A}$	$t_r$	-	400	-	ns
Fall time	$I_F = 100\text{ mA}$	$t_f$	-	800	-	ns
	$I_F = 1.5\text{ A}$	$t_f$	-	400	-	ns
Virtual source diameter		$d$	-	2.1	-	mm

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

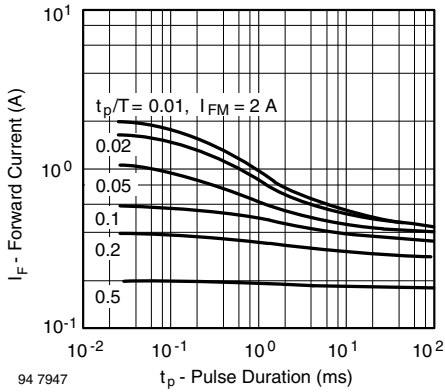


Fig. 3 - Pulse Forward Current vs. Pulse Duration

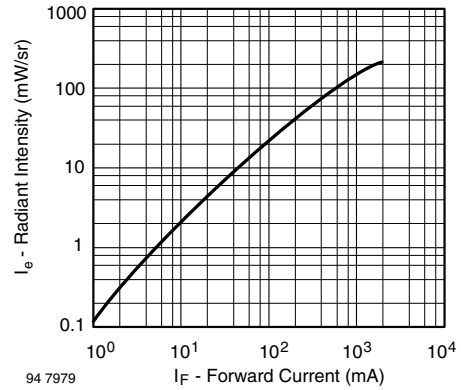


Fig. 6 - Radiant Intensity vs. Forward Current

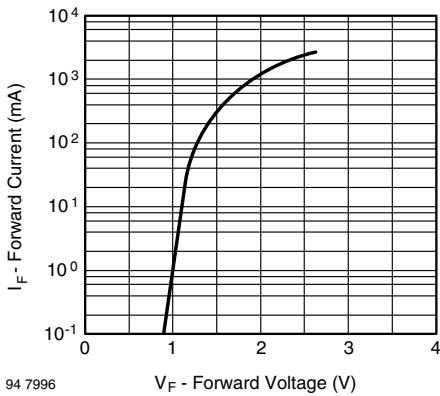


Fig. 4 - Forward Current vs. Forward Voltage

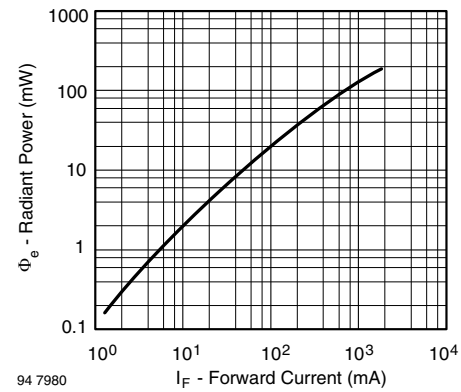


Fig. 7 - Radiant Power vs. Forward Current

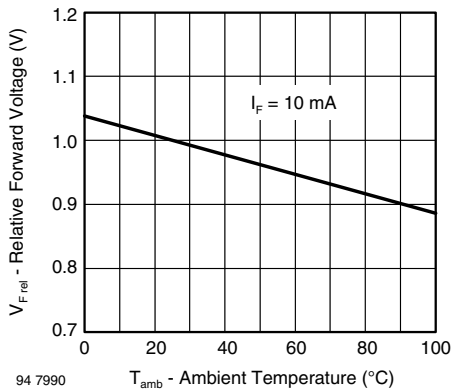


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

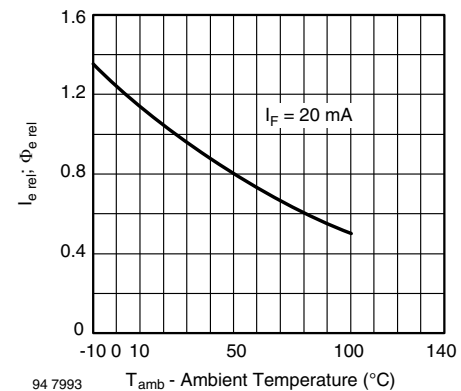


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

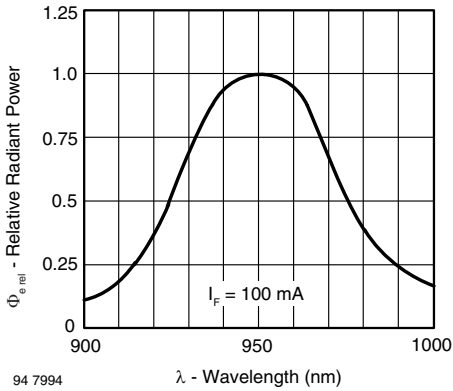


Fig. 9 - Relative Radiant Power vs. Wavelength

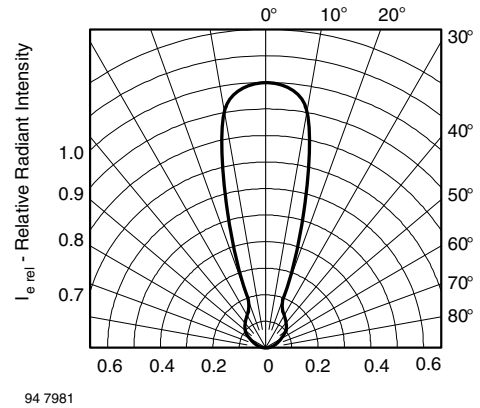
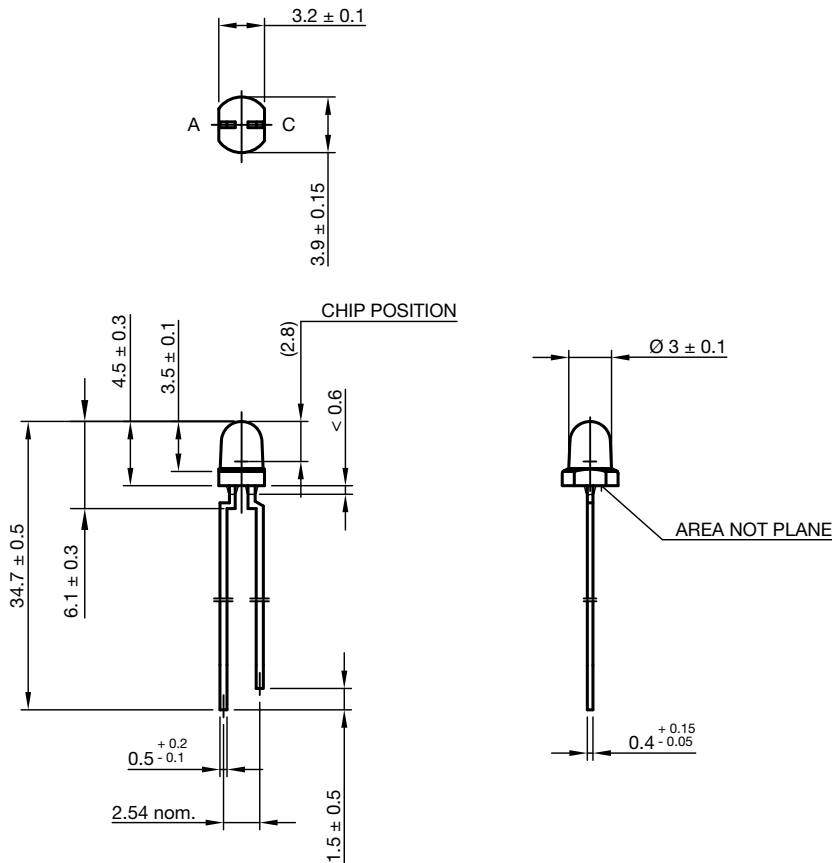


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5269.02-4  
Issue: 5; 28.07.14



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